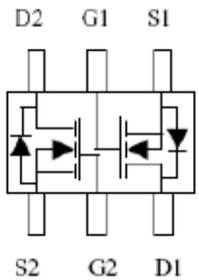
MOSFET (N-CHANNEL) **Plastic-Encapsulate Transistor**

FEATURES

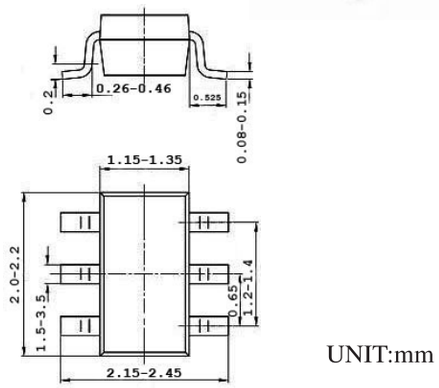
- Dual N-channel MOSFET
- Low on-resistance
- Low gate threshold voltage
- Low input capacitance
- Fast switching speed
- Low input/output leakage



MARKING: K72

SOT-363





UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

MAXIMUM RATINGS

Parameters	Symbols	Value	UNITS
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current	I_D	115	mA
Total Power Dissipation	P_D	200	mW
Junction and Storage Temperature	T_J,T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage*	$V_{(BR)DSS}$	V_{GS}=0V, I_D=10μA	60	70		V
Gate-Threshold Voltage*	$V_{th\ (GS)}$	V_{DS}=V_{GS}, I_D=250μA	1	1.5	2	V
Gate-Body Leakage*	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±10	nA
Zero Gate Voltage Drain Current*	I_{DSS}	V_{DS}=60V, V_{GS}=0V V_{DS}=60V, V_{GS}=0V, T_j=125			1 500	μA
On-State Drain Current*	$I_{D(ON)}$	V_{GS}=10V, V_{DS}=7.5V	500	1000		mA
Drain-Source On-Resistance*	$r_{DS(ON)}$	V_{GS}=5V, I_D=50mA V_{GS}=10V, I_D=500mA		3.2 4.4	7.5 13.5	Ω
Forward Tran Conductance*	g_{ts}	V_{DS}=10V, I_D=200mA	80			ms
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, f=1MHz		22	50	pF
Output Capacitance	C_{OSS}			11	25	pF
Reverse Transfer Capacitance	C_{RSS}			2	5	pF

SWITCHING

Turn-on Time	$t_{d(on)}$	V_{DD}=30V, R_L=150Ω, I_D=200mA, V_{GEN}=10V, R_G=25Ω		7	20	ns
Turn-off Time	$t_{d(off)}$			11	20	ns

*Pulse test, pulse width ≤ 300μs, duty cycle ≤ 2%